

Simulasi model : Heterojunction bipolar transistor silikon - germanium (HBT SiGe) berdasarkan pengaturan lebar stripe emiter (We)

Deskripsi Lengkap: <https://lib.ui.ac.id/detail?id=129449&lokasi=lokal>

Abstrak

Si-Ge HBTs is an electronic device having important role in developing Information and Telecommunication Technology. It can be shown by the superior performance of threshold frequency (f_r) oscillation frequency (f_{osc}) current gain (B) and minimum noise figure (F_n)....